



Sheet 1 of 1

Form PTO-1449

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SERIAL NO.

APPLICANT

M. FUNABASHI

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2825



## INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use several sheets if necessary)

## **U.S. PATENT DOCUMENTS**

Examiner Initial		Document Number Date		Name		Class	Subclass	Filing Date	
SUM- AA		4,239,661	12/16/80	Muraoka et al.	438	<del>( 252 -</del>	<del>-541→</del>	471	
1	AB	4,958,061	09/18/90	Wakabayashi et al.		219	411		
	AC	5,286,678	02/15/94	Rastogi	438	<del>437-</del>	<del>-200</del> >	301	
1	AD	5,288,651	02/22/94	Nakazawa	438	€437	<del>-31→</del>	145	
	AE	5,290,361	03/01/94	Hayashida et al.		134	2		
	AF	5,447,568	09/05/95	Hayakawa et al.	118	<del>437</del>	<del>-187→</del>	715	
	AG	5,466,389	11/14/95	Ilardi et al.	510	<del>&lt; 252 -</del>	- <del>156-&gt;</del>	175	
	AH	5,783,495	07/21/98	Li et al.		438	738		
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V	AL	6,096,650	08/2000	Robinson et al.		438	689		

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							Yes	No
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		07-153728-A	06/1995	Japan	HOIL	21/304		
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	AO	Watanabe et al., "Influence of particles/impurity metals in contamination", International Symposium on Semiconductopp. 99-102	RCA cleaning solutions on surface or Manufacturing (1994),		
	AP	Osaka and Hattori, "Influence of Initial Wafer Cleanliness Immersion SC-1 Cleaning: Limitation of Immersion-Type Semiconductor Manufacturing, Vol. 11, No. 1 (02/1998),	on Metal Removal Efficiency in Wet Cleaning", IEEE Trans. on op. 20-24		
	AQ	Ridley, Sr. et al., "Advanced Aqueous Wafer Cleaning in P Manufacturing", IEEE/SEMI Adv. Semiconductor Man. Co	ower Semiconductor Device onf. (1998), pp. 235-242		
1	AR	"Improved Organic Clean for Removing Contaminants on Semiconductor Wafer Surfaces", IBM Tech. Dis. Bulletin, March 1985			
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